TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# **TPCA8049-H**

Switching Regulator Applications Motor Drive Applications DC-DC Converter Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q<sub>SW</sub> = 13 nC (typ.)
- Low drain-source ON-resistance:  $R_{DS}$  (ON) = 6.6  $m\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 88 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A (max) (V_{DS} = 60 V)$
- Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ mA})$

### Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	60	V	
Drain-gate voltage (R	GS = 20 kΩ)	$V_{DGR}$	60	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	ID	28	Α	
Drain current	Pulsed (Note 1)	$I_{DP}$	84	A	
Drain power dissipati	on (Tc = 25°C)	$P_{D}$	45	W	
Drain power dissipati	on (t = 10 s) (Note 2a)	$P_{D}$	2.8	W	
Drain power dissipati	on (t = 10 s) (Note 2b)	P <sub>D</sub>	1.6	W	
Single-pulse avalance	ne energy (Note 3)	E <sub>AS</sub>	57	mJ	
Avalanche current		I <sub>AR</sub>	28	Α	
Repetitive avalanche (To	energy c = 25°C) (Note 4)	E <sub>AR</sub>	2.85	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C	

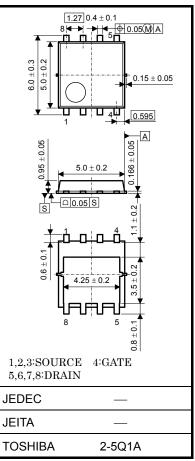
Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

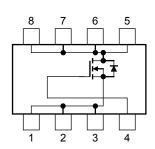
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.069 g (typ.)

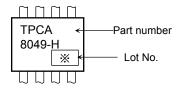
### **Circuit Configuration**



#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R <sub>th (ch-c)</sub>	2.78	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W

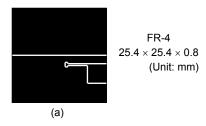
## Marking (Note 5)

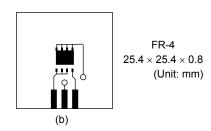


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

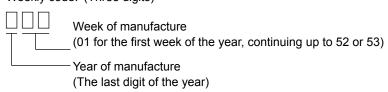




Note 3:  $V_{DD} = 24~V,~T_{Ch} = 25^{\circ}C$  (initial), L = 100  $\mu H,~R_G = 25~\Omega,~I_{AR} = 28~A$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



2



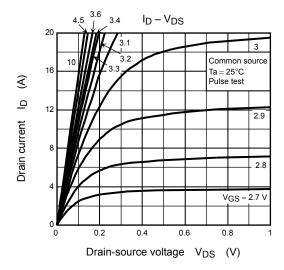
# **Electrical Characteristics (Ta = 25°C)**

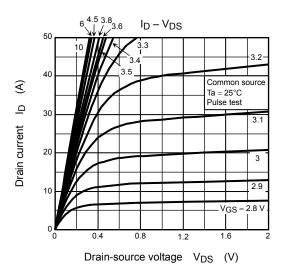
Ch	Characteristic		Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	_	_	10	μΑ
Drain source bro	akdown voltago	V <sub>(BR)</sub> DSS	$I_D = 10$ mA, $V_{GS} = 0$ V	60	_	_	V
Drain-source breakdown voltage		V <sub>(BR) DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	45	_	_	V
Gate threshold vo	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ mA}$	1.3	_	2.3	V
Drain-source ON	resistance	Б	$V_{GS} = 4.5 \text{ V}, I_D = 14 \text{ A}$		7.4	11.2	mO
Dialii-source ON	-i esistance	R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 14 A	—     —     10       60     —     —       45     —     —       1.3     —     2.3	mΩ		
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 14 A	44	88	_	S
Input capacitance	9	C <sub>iss</sub>			3545	4610	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	130	190	pF
Output capacitance		C <sub>oss</sub>		_	420	_	
Gate resistance		rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	1.0	1.5	Ω
Switching time	Rise time	t <sub>r</sub>	ACS 0 A	_	2.9	_	ns
	Turn-on time	t <sub>on</sub>			12		
	Fall time	t <sub>f</sub>	4.7.Ω W W W W W W W W W W W W W W W W W W W		5.6		
	Turn-off time	t <sub>off</sub>	$V_{DD} \approx 30 \text{ V}$ Duty $\leq$ 1%, $t_W = 10 \mu\text{s}$	_	46	_	
Total gate charge	al gate charge		$V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 28 \text{ A}$	_	55	_	
(gate-source plus	gate-drain)	Qg	V <sub>DD</sub> ≈ 48 V, V <sub>GS</sub> = 5 V, I <sub>D</sub> = 28 A	_	_ 29		
Gate-source charge 1		Q <sub>gs1</sub>		_	10	_	nC
Gate-drain ("Miller") charge		Q <sub>gd</sub>	$V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 28 \text{ A}$	_	8.5	_	
Gate switch char	ge	Q <sub>SW</sub>		_	13	_	

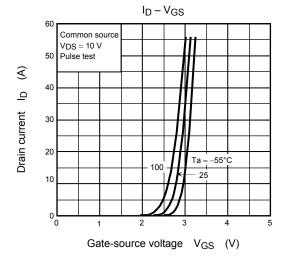
# **Source-Drain Ratings and Characteristics (Ta = 25°C)**

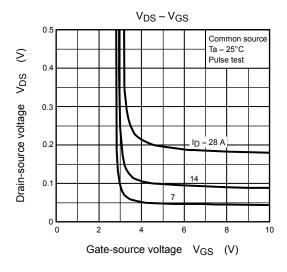
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	84	Α
Forward voltage (diode)			$V_{DSF}$	$I_{DR} = 28 \text{ A}, V_{GS} = 0 \text{ V}$			-1.2	V

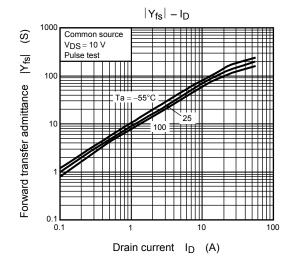
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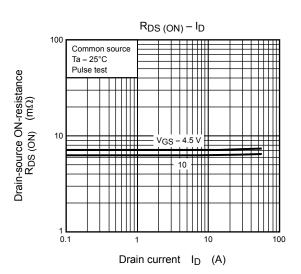


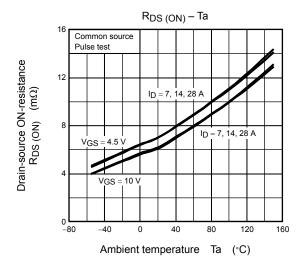


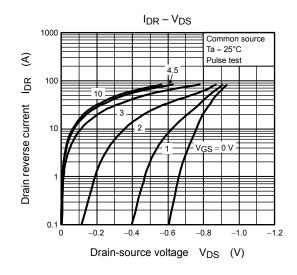


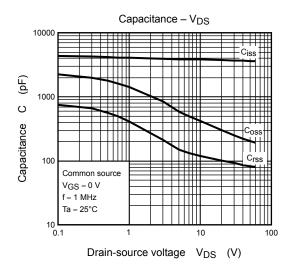


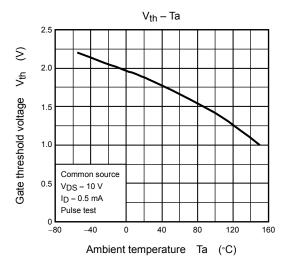


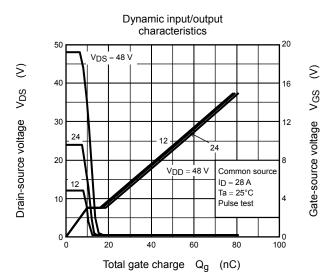




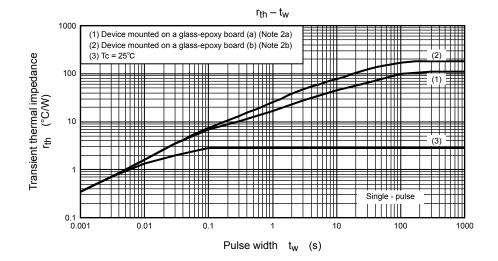


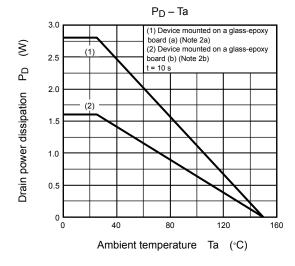


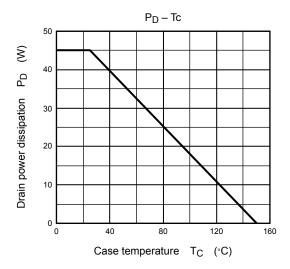


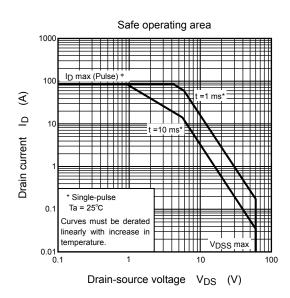


5 2009-07-03









6 2009-07-03

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